# One Cell Lithium-ion/Polymer Battery Protection IC

# **GENERAL DESCRIPTION**

The JTM54611 product is a high integration solution for lithiumion/polymer battery protection. JTM54611 contains advanced power MOSFET, high-accuracy voltage detection circuits and delay circuits. JTM54611 is put into an ultra-small DFN2X2-6 package and only one external component makes it an ideal solution in limited space of battery pack. JTM54611 has all the protection functions required in the battery application including overcharging, overdischarging, overcurrent and load short circuiting protection etc. The accurate overcharging detection voltage ensures safe and full utilization charging. The low standby current drains little current from the cell while in storage.

The device is not only targeted for digital cellular phones, but also for any other Li-lon and Li-Poly battery-powered information appliances requiring longterm battery life.

### FEATURES

Protection of Charger Reverse
Connection

Protection of Battery Cell Reverse
Connection

- Integrate Advanced Power MOSFET with Equivalent of  $45m\Omega$  RDs(ON)

- · Ultra-small DFN2X2-6 Package
- Only One External Capacitor Required
- · Over-temperature Protection
- Overcharge Current Protection
- Two-step Overcurrent Detection: -Overdischarge Current -Load Short Circuiting
- Charger Detection Function
- · 0V Battery Charging Function
- Delay Times are generated inside
- · High-accuracy Voltage Detection
- · Low Current Consumption
  - Operation Mode: 2.8µ A typ.
  - Power-down Mode: 0.1µ A typ.

•RoHS Compliant and Lead (Pb) Free

### APPLICATIONS

One-Cell Lithium-ion Battery Pack Lithium-Polymer Battery Pack

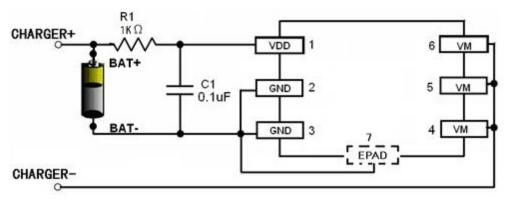


Figure 1. Typical Application Circuit

### **ORDERING INFORMATION**

PART NUMBER	Packa ge	Overcharge Detection Voltage [Vcu] (V)	Overcharge Release Voltage [VcL] (V)	Overdischarge Detection Voltage [VDL] (V)	Overdischarge Release Voltage [VDR] (V)	Overcurrent Detection Current [lov1] (A)	Top Mark
JTM54611	DFN2 X2-6	4.30	4.10	2.80	3.0	0.9	6166ISYW (note)

Note: "YW" is manufacture date code, "Y" means the year, "W" means the week

## **PIN CONFIGURATION**

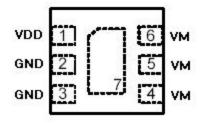




Figure 2. PIN Configuration

### **PIN DESCRIPTION**

JTM54611 PIN NUMBER	PIN NAME	PIN DESCRIPTION
1	VDD	Power Supply
2, 3	GND	Ground, connect the negative terminal of the battery to this pin
4, 5, 6	VM	The negative terminal of the battery pack. The internal FET switch connects this terminal to GND
7	EPAD	Please connect EPAD with mass metal GND

### **ABSOLUTE MAXIMUM RATINGS**

(Note: Do not exceed these limits to prevent damage to the device. Exposure to absolute maximum rating conditions for long periods may affect device reliability.)

PARAMETER	VALUE	UNIT
VDD input pin voltage	-0.3 to 6	V
VM input pin voltage	-6 to 10	V
Operating Ambient Temperature	-40 to 85	°C
Maximum Junction Temperature	125	°C
Storage Temperature	-55 to 150	°C

Lead Temperature (Soldering, 10 sec)	300	°C
Power Dissipation at T=25°C	0.4	W
Package Thermal Resistance (Junction to Ambient) $\theta_{JA}$	250	°C /W
Package Thermal Resistance (Junction to Case) θια	130	°C /W
ESD	2000	V

## **ELECTRICAL CHARACTERISTICS**

Typicals and limits appearing in normal type apply for TA = 25oC, unless otherwise specified

OperationVM =0VImage: Constraint of the second secon	Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Overcharge Detection VoltageVcuInternalInternalOvercharge Release VoltageVcL4.054.104.15Overdischarge Detection VoltageVbL2.72.82.9Overdischarge Release VoltageVbR2.93.03.1Overdischarge Release VoltageVbR2.93.03.1Charger Detection Voltage*VcHA-0.060Detection Current10V1VbD=3.6V0.40.91.5Detection Current10V1VbD=3.6V102030Detection10V1VbD=3.5V102030Detection10PEVbD=3.5V102.86µCurrent Consumption10PEVbD=3.5V0.11µDown1PENVbD=3.5V0.11µDown1PENVbD=3.5V320101VM Internal Resistance*RVMDVbD=3.5V32010Internal Resistance between*RVMDVbD=3.5V10011VM and Voo*RVMSVbD=2.0V10011Internal Resistance*RVMDVbD=3.5V32011FET on Resistance*RVMSVbD=2.0V10011FET on Resistance*RDS(ON)VbD=3.6V IVM =1.0A404555rEquivalent FET on Resistance*RDS(ON)VbD=3.6V IVM =1.0A404555r	Detection Voltage						
Overcharge Release Voltage         VCL         Image: Constraint of the second s	Overcharge Detection Voltage	Vcu		4.25	4.30	4.35	V
Overdischarge Detection Voltage       VbL       Image: Construct the set of the set	Overcharge Release Voltage	Vcl		4.05	4.10	4.15	V
Overdischarge Release Voltage         Vbr         Charger         Charg	Overdischarge Detection Voltage	Vdl		2.7	2.8	2.9	v
Detection CurrentOverdischarge Current1 DetectionIIOV1VDD=3.6V0.40.91.5Load Short-Circuiting Detection*ISHORTVDD=3.5V102030Current ConsumptionIOPEVDD=3.5V102030Current Consumption in Normal OperationIOPEVDD=3.5V2.86µCurrent Consumption in power DownIPDNVDD=2.0V0.111µVM Internal Resistance*RVMDVDD=3.5V320101Internal Resistance between VM and VDD*RVMSVDD=2.0V10011Internal Resistance between VM and GND*RVMSVDD=2.0V10011FET on Resistance*RVMSVDD=3.5V32011Equivalent FET on Resistance*RDS(ON)VDD=3.6V IVM =1.0A404555r	Overdischarge Release Voltage	Vdr		2.9	3.0	3.1	V
Overdischarge Current1 DetectionIIOV1VDD=3.6V0.40.91.5Load Short-Circuiting Detection*ISHORTVDD=3.5V1020300Current ConsumptionCurrent Consumption in Normal OperationIOPEVDD=3.5V VM =0V2.86µCurrent Consumption in power DownIPDNVDD=2.0V VM pin floating0.111µVM Internal Resistance*RVMDVDD=3.5V VM=1.0V32011µVM and VDD*RVMDVDD=3.5V VM=1.0V10011Internal Resistance between And GND*RVMSVDD=2.0V VDD=2.0V VM=1.0V10011FET on Resistance*RVMSVDD=2.0V VD=2.0V VM=1.0V10011FET on Resistance*RDS(ON)VDD=3.6V IVM =1.0A404555r	Charger Detection Voltage	*Vcha			-0.06		V
Load Short-Circuiting Detection*ISHORTVbD = 3.5V102030Current ConsumptionIopeVbD = 3.5V102030Current Consumption in Nomal OperationIopeVbD = 3.5V VM = 0V2.86µCurrent Consumption in power DownIopeVbD = 2.0V VM pin floating0.11µVM Internal ResistanceIPDNVbD = 3.5V VM = 0.V3200.11µVM Internal Resistance between VM and VbD*RVMDVbD = 3.5V VM = 1.0V320IInternal Resistance between VM and GND*RVMSVbD = 2.0V VM = 1.0V100IFET on Resistance*RVMSVbD = 2.0V VM = 1.0V100IFET on Resistance*RDS(ON)VbD = 3.6V Ivm = 1.0A404555r	Detection Current						
DetectionImage: constraint of the systemDetectionImage: constraint of the systemCurrent Consumption in Normal OperationIope VDEVDD=3.5V VM=0V2.86µCurrent Consumption in power DownIPDNVDD=2.0V VM pin floating0.111µVM Internal ResistanceVDD=3.5V VM and VDD320 VM=1.0V320 Image: constraint of the systemImage: constraint of the systemIm	Overdischarge Current1 Detection		VDD=3.6V	0.4	0.9	1.5	A
Current Consumption in Nomal OperationIOPEVDD=3.5V VM =0V2.86µCurrent Consumption in power DownIPDNVDD=2.0V VM pin floating0.11µVM Internal ResistanceInternal Resistance between VM and VDD*RvMDVDD=3.5V VM=1.0V320µInternal Resistance between VM and GND*RvMSVDD=2.0V VD=2.0V VM=1.0V100µFET on Resistance*RvMSVDD=2.0V VD=2.0V VM=1.0V100µFET on Resistance*RDS(ON)VDD=3.6V IVM =1.0A404555r		*ISHORT	Vdd=3.5V	10	20	30	A
OperationVM =0 VImage: Construction of the second se							
Down       VM pin floating       Image: Comparison of the second		IOPE			2.8	6	μA
Internal Resistance between       *RVMD       VDD=3.5V       320       I         VM and VDD       VDD=1.0V       VM=1.0V       100       I         Internal Resistance between VM       *RVMS       VDD=2.0V       100       I         and GND       VM=1.0V       VM=1.0V       100       I         FET on Resistance       *RDS(ON)       VDD=3.6V IVM = 1.0A       40       45       55		IPDN			0.1	1	μA
VM and VDD     VM=1.0V       Internal Resistance between VM and GND     *RvMs       VD=2.0V VM=1.0V     100       FET on Resistance       Equivalent FET on Resistance       *RDS(ON)       VD=3.6V IVM =1.0A       40       45       55	VM Internal Resistance						
and GND         VM=1.0V         Image: Non-Liev		*R∨мо			320		kΩ
Equivalent FET on Resistance         *RDS(ON)         VDD=3.6V IVM =1.0 A         40         45         55         r		*R∨мs			100		kΩ
	FET on Resistance						
Over Temperature Protection	Equivalent FET on Resistance	*RDS(ON)	VDD=3.6V IVM =1.0A	40	45	55	mΩ
	Over Temperature Protection	1		1	1	1	L
Over Temperature Protection *T <sub>SHD+</sub> 120	Over Temperature Protection	*Tshd+			120		0
Over Temperature Recovery Degree *T <sub>SHD-</sub> 100	Over Temperature Recovery Degree	*TsнD-			100		°C

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Detection Delay Time					
Overcharge Voltage Detection Delay Time	tcu		130	200	mS
Overdischarge Voltage Detection Delay Time	toL		40	60	mS
Overdischarge Current Detection Delay Time	tiov	VDD=3.5V	10	20	mS
Load Short-Circuiting Detection Delay Time	*tsнок т	VDD=3.5V	75	150	uS

Note: \* --- The parameter is guaranteed by design.

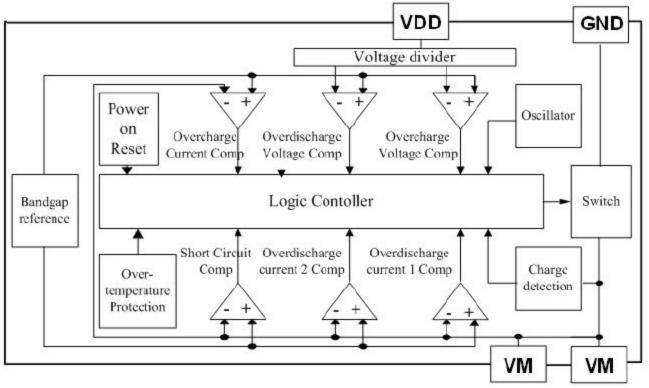


Figure 3. Functional Block Diagram

## FUNCTIONAL DESCRIPTION

The JTM54611 monitors the voltage and current of a battery and protects it from being damaged due to overcharge voltage, overdischarge voltage, overdischarge current, and short circuit conditions by disconnecting the battery from the load or charger. These functions are required in order to operate the battery cell within specified limits.

The device requires only one external capacitor. The MOSFET is integrated and its  $R_{DS(ON)}$  is as low as  $45m\Omega$  typical.

#### Normal operating mode

If no exception condition is detected, charging and discharging can be carried out freely. This condition is called the normal operating mode.

#### **Overcharge Condition**

When the battery voltage becomes higher than the overcharge detection voltage ( $V_{CU}$ ) during charging under normal condition and the state continues for the overcharge detection delay time ( $t_{CU}$ ) or longer, the JTM54611 turns the charging control FET off to stop charging. This condition is called the overcharge condition. The overcharge condition is released in the following two cases:

1, When the battery voltage drops below the overcharge release voltage (VcL), the JTM54611 turns the charging control FET on and returns to the normal condition. 2. When a load is connected and discharging starts, the JTM54611 turns the charging control FET on and returns to the normal condition. The release mechanism is as follows: the discharging current flows through an internal parasitic diode of the charging FET immediately after a load is connected and discharging starts, and the VM pin voltage increases about 0.7 V (forward voltage of the diode) from the GND pin voltage momentarily. The JTM54611 detects this voltage and releases the overcharge condition. Consequently, in the case that the battery voltage is equal to or lower than the overcharge detection voltage (Vcu), the JTM54611 returns to the normal condition immediately, but in the case the battery voltage is higher than the overcharge detection voltage (Vcu), the chip does not return to the normal condition until the battery voltage drops below the overcharge detection voltage (Vcu) even if the load is connected. In addition, if the VM pin voltage is equal to or lower than the overcurrent 1 detection voltage when a load is connected and discharging starts, the chip does not return to the normal condition.

**Remark** If the battery is charged to a voltage higher than the overcharge detection voltage (Vcu) and the battery voltage does not drops below the overcharge detection voltage (VCU) even when a heavy load, which causes an overcurrent, is connected, the overcurrent 1 and overcurrent 2 do not work until the battery voltage drops below the overcharge detection voltage (VCU). Since an actual battery has, however, an internal impedance of several dozens of m $\Omega$ , and the battery voltage drops immediately after a heavy load which causes an overcurrent is connected, the overcurrent 1 and overcurrent 2 work. Detection of load short-circuiting works regardless of the battery voltage.

#### **Overdischarge Condition**

When the battery voltage drops below the overdischarge detection voltage ( $V_{DL}$ ) during discharging under normal condition and it continues for the overdischarge detection delay time ( $t_{DL}$ ) or longer, the JTM54611 turns the discharging control FET off and stops discharging. This condition is called overdischarge condition. After the discharging control FET is turned off, the VM pin is pulled up by the RVMD resistor

between VM and VDD in JTM5461I. Meanwhile when VM is bigger than 1.5 V (typ.) (the load short-circuiting detection voltage), the current of the chip is reduced to the power-down current (IPDN). This condition is called power-down condition. The VM and VDD pins are shorted by the RVMD resistor in the IC under the overdischarge and power-down conditions. The power-down condition is released when a charger is connected and the potential difference between VM and VDD becomes 1.3 V (typ.) or higher (load shortcircuiting detection voltage). At this time, the FET is still off. When the battery voltage becomes the overdischarge detection voltage ( $V_{DL}$ ) or higher (see note),

the JTM54611 turns the FET on and changes to the normal condition from the overdischarge condition.

**Remark** If the VM pin voltage is no less than the charger detection voltage (VCHA), when the battery under overdischarge condition is connected to a charger, the overdischarge condition is released (the discharging control FET is turned on) as usual, provided that the battery voltage reaches the overdischarge release voltage (VDU) or higher.

#### **Overcurrent Condition**

When the discharging current becomes equal to or higher than a specified value (the VM pin voltage is equal to or higher than the overcurrent detection voltage) during discharging under normal condition and the state continues for the overcurrent detection delay time or longer, the

JTM5461 lturns off the discharging control FET to stop discharging. This condition is called overcurrent condition. (The overcurrent

includes overcurrent, or load shortcircuiting.)

The VM and GND pins are shorted internally by the RVMS resistor under the overcurrent condition. When a load is connected, the VM pin voltage equals the VDD voltage due to the load.

The overcurrent condition returns to the normal condition when the load is released and the impedance between the B+ and B-pins becomes higher than the automatic recoverable impedance. When the load is removed, the VM pin goes back to the GND potential since the VM pin is shorted the GND pin with the RVMS resistor. Detecting that the VM pin potential is lower than the overcurrent detection voltage (VIOV1), the IC returns to the normal condition.

#### Abnormal Charge Current Detection

If the VM pin voltage drops below the charger detection voltage (V<sub>CHA</sub>) during charging under the normal condition and it continues for the overcharge detection delay time (t<sub>CU</sub>) or longer, the JTM54611 turns the charging control FET off and stops charging. This action is called abnormal charge current detection. Abnormal charge current detection works when the discharging control FET is on and the VM pin voltage drops below the charger detection voltage (V<sub>CHA</sub>). When an abnormal charge current flows into a battery in the overdischarge condition, the

JTM5461I consequently turns the charging control FET off and stops charging after the battery voltage becomes the overdischarge detection voltage and the overcharge detection delay time (tcu) elapses.

Abnormal charge current detection is released when the voltage difference between VM pin and GND pin becomes lower than the charger detection voltage (V<sub>CHA</sub>) by separating the charger. Since the 0 V battery charging function has higher priority than the abnormal charge current detection function, abnormal charge current may not be detected by the product with the 0 V battery charging function while the battery voltage is low.

#### Load Short-circuiting condition

If voltage of VM pin is equal or below short circuiting protection voltage (V<sub>SHORT</sub>), the JTM54611 will stop discharging and battery is disconnected from load. The maximum delay time to switch current off is t<sub>SHORT</sub>. This status is released when voltage of VM pin is higher than short protection voltage (V<sub>SHORT</sub>), such as when disconnecting the load.

#### **Delay Circuits**

The detection delay time for overdischarge current 2 and load short-circuiting starts when overdischarge current 1 is detected. As soon as overdischarge current 2 or load short-circuiting is detected over detection delay time for overdischarge current 2 or

load short-circuiting, the JTM54611 stops discharging. When battery voltage falls below overdischarge detection voltage due

to overdischarge current, the JTM54611 stop discharging by overdischarge current detection. In this case the recovery of battery voltage is so slow that if battery voltage after overdischarge voltage detection delay

# JTM5461I

time is still lower than overdischarge detection voltage, the JTM54611 shifts to power-down.

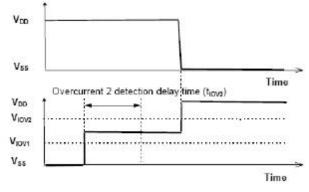


Figure 4. Overcurrent delay time

**OV Battery Charging Function** (1) (2) (3) This function enables the charging of a connected battery whose voltage is 0 V by self-discharge. When a charger having 0 V battery start charging charger voltage (V<sub>OCHA</sub>) or higher is connected between B+ and B- pins, the charging control FET gate is fixed to VDD potential. When the voltage between the gate and the source of the charging control FET becomes equal to or higher than the turn-on voltage by the charger voltage, the charging control FET is turned on to start charging. At this time, the discharging control FET is off and the charging current flows through the internal parasitic diode in the discharging control FET. If the battery voltage becomes equal to or higher than the overdischarge release voltage (V<sub>DU</sub>), the normal condition returns.

#### Note

(1) Some battery providers do not recommend charging of completely discharged batteries. Please refer to battery providers before the selection of 0 V battery charging function.

(2) The 0V battery charging function has higher priority than the abnomal charge current detection function. Consequently, a product with the 0 V battery charging function charges a battery and abnomal charge current cannot be detected during the battery voltage is low (at most 1.8 V or lower).
(3) When a battery is connected to the IC for the first time, the IC may not enter the normal condition in which discharging is possible. In this case, set the VM pin voltage equal to the GND voltage (short the VM and GND pins or connect a charger) to enter the normal condition.

### **TIMING CHART**

1. Overcharge and overdischarge detection

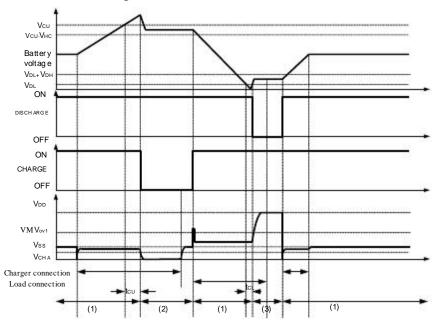
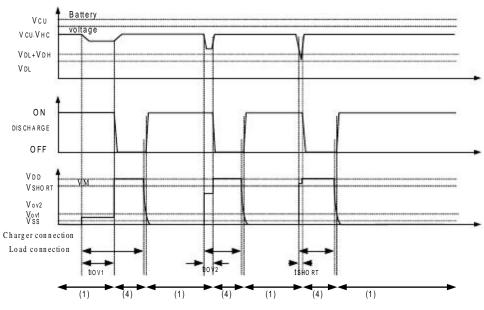
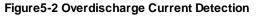


Figure 5-1 Overcharge and Overdischarge Voltage Detection

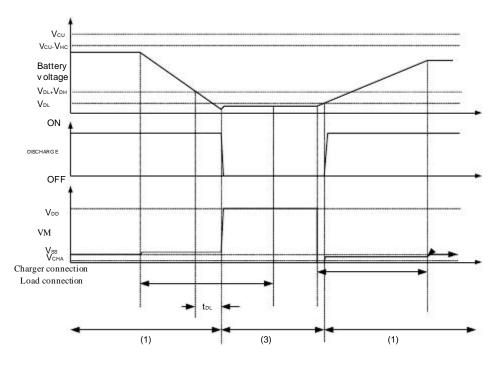
#### 2. Overdischarge current detection





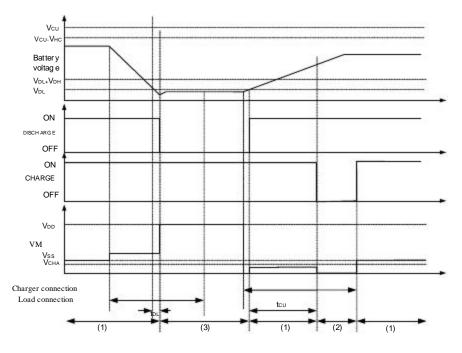
Remark: (1) Normal condition (2) Overcharge voltage condition (3) Overdischarge voltage condition (4) Overcurrent condition

#### 3. Charger Detection





#### 4. Abnormal Charger Detection





Remark: (1) Normal condition (2) Overcharge voltage condition (3) Overdischarge voltage condition (4) Overcurrent condition

### TYPICAL APPLICATION

As shown in Figure 6, the bold line (high-lined) is the high density current path which must be kept as short as possible. For thermal management, ensure that these trace widths are adequate. C1 is a decoupling capacitor which should be placed as close as possible to JTM54611.

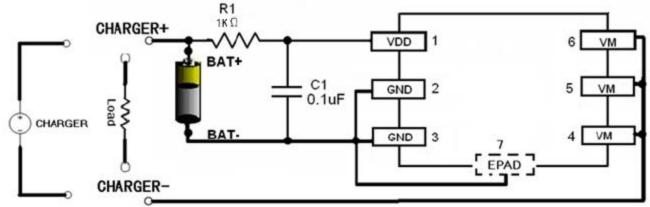


Fig 6 JTM54611 in a Typical Battery Protection Circuit

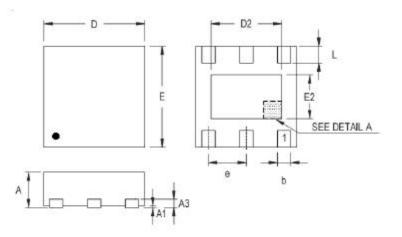
#### Precautions

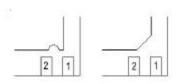
• Pay attention to the operating conditions for input/output voltage and load current so that the power loss in JTM54611 does not exceed the power dissipation of the package.

•Do not apply an electrostatic discharge to this JTM54611 that exceeds the performance ratings of the built-in electrostatic protection circuit.

## PACKAGE OUTLINE

DFN-6L 2MM X 2MM PACKAGE OUTLINE AND DIMENSIONS





DETAIL A Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

SYMBOL	Dimen Millim	sion in neters	Dimension in Inches		
	MIN MAX		MIN	MAX	
A	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A3	0.175	0.250	0.007	0.010	
b	0.200	0.350	0.008	0.014	
D	1.950	2.050	0.077	0.081	
D2	1.000	1.450	0.039	0.057	
E	1.950	2.050	0.077	0.081	
E2	0.500 0.850		0.020	0.033	
е	0.650		0.026		
L	0.300 0.400		0.012	0.016	